NEC

NPN SILICON TRANSISTOR 2SC2002

DESCRIPTION

The 2SC2002 is designed for use in driver stage of high voltage

audio equipments.

FEATURES

High total power dissipation.

Рт

: 600 mW

High h_{FE} and high voltage.

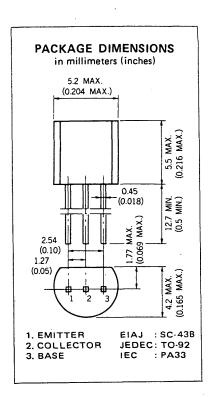
 h_{FE} (I_C = 50 mA) : 200 TYP.

VCEO

: 60 V

ABSOLUTE MAXIMUM RATINGS

| Maximum Temperatures | | | | | | | | |
|--|------|--|--|--|--|--|--|--|
| Storage Temperature55 to +15 | o °c | | | | | | | |
| Junction Temperature +150 °C Maxi | mum | | | | | | | |
| Maximum Power Dissipation (Ta = 25 °C) | | | | | | | | |
| Total Power Dissipation 600 | mW | | | | | | | |
| Maximum Voltages and Currents (Ta = 25 °C) | | | | | | | | |
| V _{CBO} Collector to Base Voltage | ٧ | | | | | | | |
| V _{CEO} Collector to Emitter Voltage 60 | V | | | | | | | |
| V _{EBO} Emitter to Base Voltage 5.0 | V | | | | | | | |
| Ic Collector Current | mΑ | | | | | | | |
| IB Base Current | mA | | | | | | | |
| | | | | | | | | |



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

| SYMBOL | CHARACTERISTIC | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS |
|-----------|-------------------------------|------|------|------|------|---|
| hFE1* | DC Current Gain | 90 | 200 | 400 | | $V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$ |
| hFE2* | DC Current Gain | 30 | 80 | | _ | $V_{CE} = 2.0 \text{ V, } I_{C} = 300 \text{ mA}$ |
| Cob | Collector to Base Capacitance | | 7.0 | 15 | pF | $V_{CB} = 6.0 \text{ V}, I_E = 0$ f = 1.0 MHz |
| fΤ | Gain Bandwidth Product | 50 | 140 | | MHz | $V_{CE} = 6.0 \text{ V}, I_{E} = -10 \text{ mA}$ |
| VBE* | Base to Emitter Voltage | 600 | 645 | 700 | mV | $V_{CE} = 6.0 \text{ V}, I_{C} = 10 \text{ mA}$ |
| VCE(sat)* | Collector Saturation Voltage | | 0.15 | 0.6 | V | $I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$ |
| VBE(sat)* | Base Saturation Voltage | | 0.86 | 1.2 | V | $I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$ |
| Ісво | Collector Cutoff Current | | | 100 | nΑ | $V_{CB} = 60 \text{ V, } I_{E} = 0$ |
| IEBO | Emitter Cutoff Current | | | 100 | nA | V _{EB} = 5.0 V, I _E = 0 |

[•]Pulsed PW \leq 350 μ s, duty cycle \leq 2.0 %.

Classification of hFE1

| Rank | М | . L | К |
|-------|----------|-----------|-----------|
| Range | 90 – 180 | 135 — 270 | 200 – 400 |

hFE Test Conditions : VCE = 1.0 V, IC = 50 mA

TYPICAL CHARACTERISTICS (Ta = 25 °C unless otherwise noted)

